

Chroma Amplifier Transistor (300V, 0.1A)

2SC4061K / 2SC3415S / 2SC4015 / 2SC3271F

●Features

- 1) High breakdown voltage. ($BV_{CEO}=300V$)
- 2) Low collector output capacitance.
(Typ. 3pF at $V_{CB}=30V$)
- 3) Ideal for chroma circuit.

●Absolute maximum ratings ($T_a=25^\circ C$)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	V_{CBO}	300	V	
Collector-emitter voltage	V_{CEO}	300	V	
Emitter-base voltage	V_{EBO}	5	V	
Collector current	I_C	100	mA	
Collector power dissipation	P_C	2SC4061K	0.2	W
		2SC3415S	0.3	
		2SC4015	1	
		2SC3271F	1.2	
Junction temperature	T_J	150	$W(T_C=25^\circ C)$ $^\circ C$	
Storage temperature	T_{stg}	-55~+150	$^\circ C$	

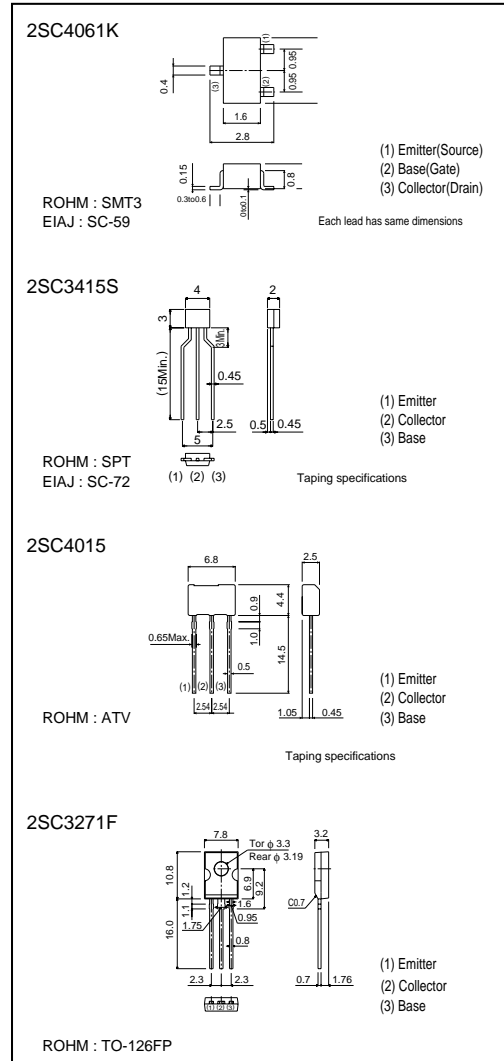
* Printed circuit board 1.7mm thick, collector plating 1cm² or larger.

●Packaging specifications and hFE

Type	2SC4061K	2SC3415S	2SC4015	2SC3271F
Package	SMT3	SPT	ATV	TO-126FP
hFE	NP	NP	N	N
Marking	AN*	-	-	-
Code	T146	TP	TV2	-
Basic ordering unit (pieces)	3000	5000	2500	1000

* Denotes hFE

●External dimensions (Units: mm)



●Electrical characteristics ($T_a=25^\circ C$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	300	-	-	V	$I_C=50\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	300	-	-	V	$I_C=100\mu A$
Emitter-base breakdown voltage	BV_{EBO}	5	-	-	V	$I_E=50\mu A$
Collector cutoff current	I_{CBO}	-	-	0.5	μA	$V_{CB}=200V$
Emitter cutoff current	I_{EBO}	-	-	0.5	μA	$V_{EB}=4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-	2	V	$I_C/I_E=50mA/5mA$
DC current	hFE	56	-	180	-	$V_{CE}=10V/10mA$
transfer ratio		56	-	120	-	
Gain bandwidth product	ft	50	100	-	MHz	$V_{CE}=30V, I_E=10mA, f=100MHz$
Collector output capacitance	Cob	-	3	-	pF	$V_{CB}=30V, I_E=0A, f=1MHz$